



HIGH VOLTAGE/HIGH SPEED NPN POWER TRANSISTORS

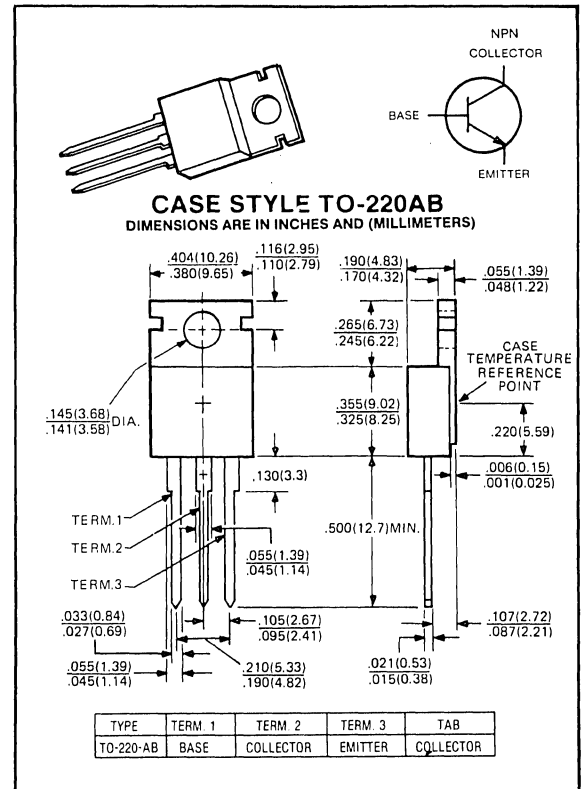
**MJE13070
MJE13071**

**400-450 VOLTS
5 AMP, 80 WATTS**

The MJE13070 and MJE13071 are high-voltage, high-speed power switching transistors, designed for use with inductive circuits, including: switching regulators, inverters, solenoid and relay drivers, motor controls, deflection circuits and other line-operated switching applications.

Features:

- **Fast Turn-Off Times:**
 - 100 ns inductive fall time @ 25°C (Typ)
 - 150 ns inductive crossover time @ 25°C (Typ)
 - 400 ns inductive storage time @ 25°C (Typ)
- **Operating temperature range -65 to +150°C**
- **100°C Performance Specified for:**
 - Switching times with inductive loads —
 - 50 ns inductive fall time (Typ)
 - Saturation voltages
 - Leakage currents



maximum ratings ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

RATING	SYMBOL	MJE13070	MJE13071	UNITS
Collector-Emitter Voltage	V_{CEO}	400	450	Volts
Collector-Emitter Voltage	V_{CEV}	650	750	Volts
Emitter Base Voltage	V_{EB}	6.0	6.0	Volts
Collector Current — Continuous	I_C	5.0	5.0	A
Peak (Repetitive) ⁽¹⁾	I_{CM}	8.0	8.0	
Base Current — Continuous	I_B	2.0	2.0	A
Peak (Non-Repetitive) ⁽¹⁾	I_{BM}	4.0	4.0	
Total Power Dissipation @ $T_c = 25^\circ\text{C}$	P_D	80	80	Watts
@ $T_c = 100^\circ\text{C}$		32	32	
Derate above 25°C		0.64	0.64	W/°C
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +150	-65 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.56	1.56	°C/W
Maximum Lead Temperature for Soldering Purpose: 1/8" from Case for 5 Seconds	T_L	260	260	°C

(1) Pulse Test: Pulse Width = 5ms. Duty Cycle ≤ 10%.

electrical characteristics ($T_C = 25^\circ\text{C}$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics⁽¹⁾

Collector-Emitter Sustaining Voltage ($I_C = 100\text{mA}$, $I_B = 0$)	MJE13070 MJE13071	$V_{CEO(sus)}$	400 450	— —	— —	Volts
Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{V}$) ($V_{CEV} = \text{Rated Value}$, $V_{BE(off)} = 1.5\text{V}$, $T_C = 100^\circ\text{C}$)		I_{CEV}	— —	— —	0.5 2.5	mA
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEV}$, $R_{BE} = 50\Omega$, $T_C = 100^\circ\text{C}$)		I_{CER}	—	—	3.0	mA
Emitter Cutoff Current ($V_{EB} = 6.0\text{V}$, $I_C = 0$)		I_{EBO}	—	—	1.0	mA

second breakdown

Second Breakdown with Base Forward Biased	$I_{S/b}$	SEE FIGURE 12
Clamped Inductive SOA with Base Reversed Bias	RBSOA	SEE FIGURE 13

on characteristics⁽¹⁾

DC Current Gain ($I_C = 3.0\text{A}$, $V_{CE} = 5.0\text{V}$)	h_{FE}	8.0	—	—	—
Collector-Emitter Saturation Voltage ($I_C = 3.0\text{A}$, $I_B = 0.6\text{A}$) ($I_C = 5.0\text{A}$, $I_B = 1.0\text{A}$) ($I_C = 3.0\text{A}$, $I_B = 0.6\text{A}$, $T_C = 100^\circ\text{C}$)	$V_{CE(sat)}$	— — —	— — —	1.0 3.0 2.0	V
Base-Emitter Saturation Voltage ($I_C = 3.0\text{A}$, $I_B = 0.6\text{A}$) ($I_C = 3.0\text{A}$, $I_B = 0.6\text{A}$, $T_C = 100^\circ\text{C}$)	$V_{BE(sat)}$	— —	— —	1.5 1.5	V

dynamic characteristics

Output Capacitance ($V_{CB} = 10\text{V}$, $I_E = 0\text{A}$, $f_{test} = 1.0\text{kHz}$)	C_{ob}	—	—	250	pF
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switching characteristics

Resistive Load							
Delay Time	$(V_{CC} = 250\text{V}$, $I_C = 3.0\text{A}$ $I_{B1} = 0.4\text{A}$, $t_p = 30\mu\text{s}$ Duty Cycle $< 2\%$, $V_{BE(OFF)} = 5.0\text{V}$)	t_d	—	0.03	0.05	μs	
Rise Time		t_r	—	0.10	0.40		
Storage Time		t_s	—	0.40	1.50		
Fall Time		t_f	—	.175	0.50		
Inductive Load, Clamped							
Storage Time	$I_C(pk) = 3.0\text{A}$ $I_{B1} = 0.4\text{A}$ $V_{BE(off)} = 5.0\text{V}$ $V_{CE(pk)} = 250\text{V}$	$(T_J = 100^\circ\text{C})$	t_{sv}	—	0.70	2.0	μs
Crossover Time			t_c	—	0.28	0.50	
Fall Time		t_{fi}	—	0.15	0.30		
Storage Time		$(T_J = 25^\circ\text{C})$	t_{sv}	—	0.40	—	
Crossover Time			t_c	—	0.15	—	
Fall Time			t_{fi}	—	0.10	—	

(1) Pulse Test: Pulse Width - $300\mu\text{s}$ Duty Cycle $\leq 2\%$.

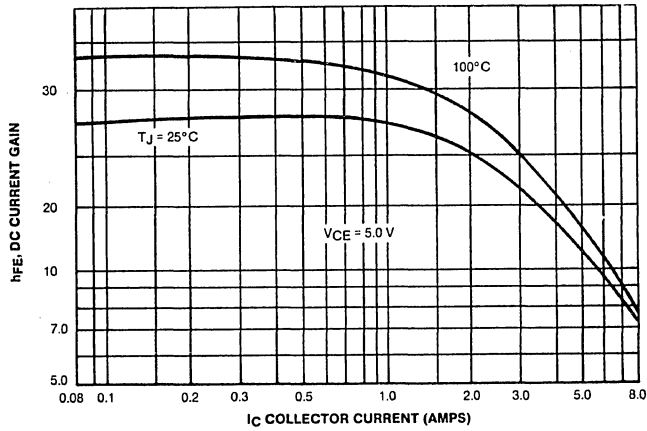


FIGURE 1 — DC CURRENT GAIN

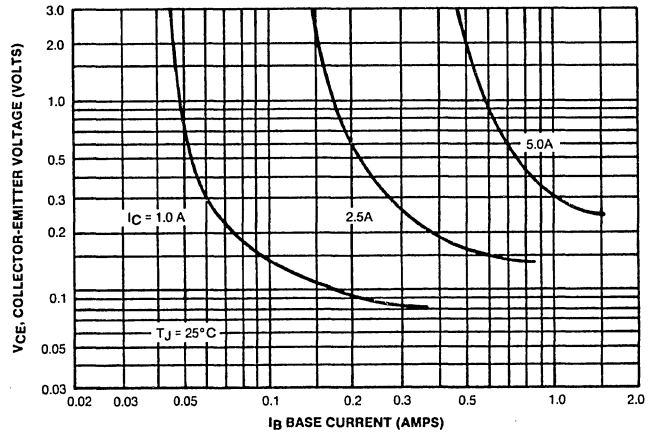


FIGURE 2 — COLLECTOR SATURATION REGION

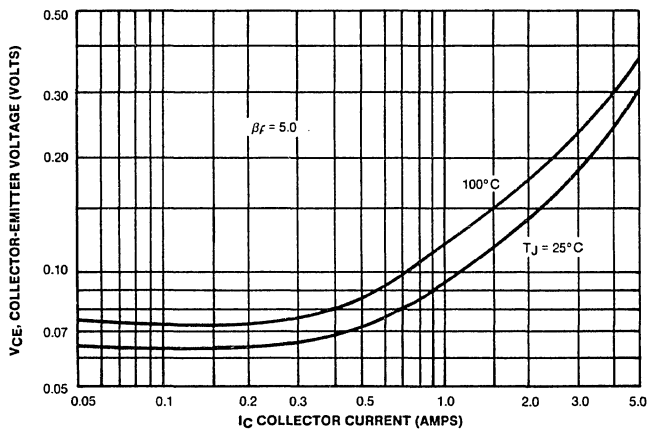


FIGURE 3 — COLLECTOR-EMITTER SATURATION VOLTAGE

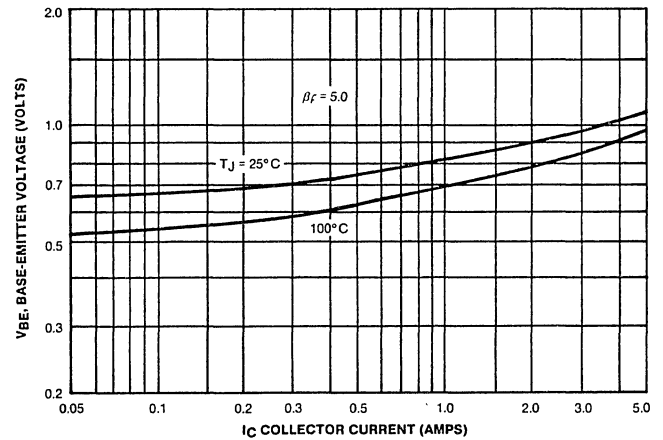


FIGURE 4 — BASE-EMITTER VOLTAGE

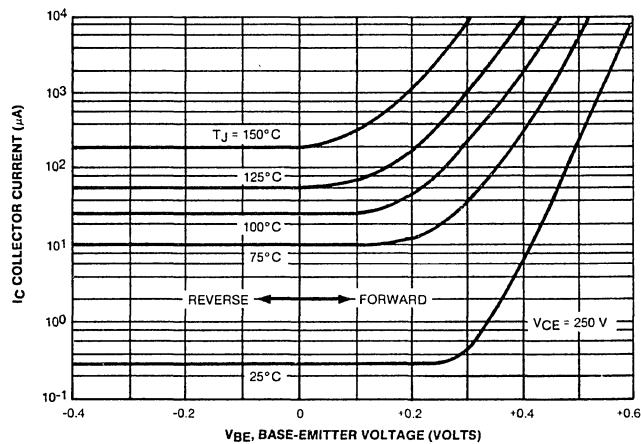


FIGURE 5 — COLLECTOR CUTOFF REGION

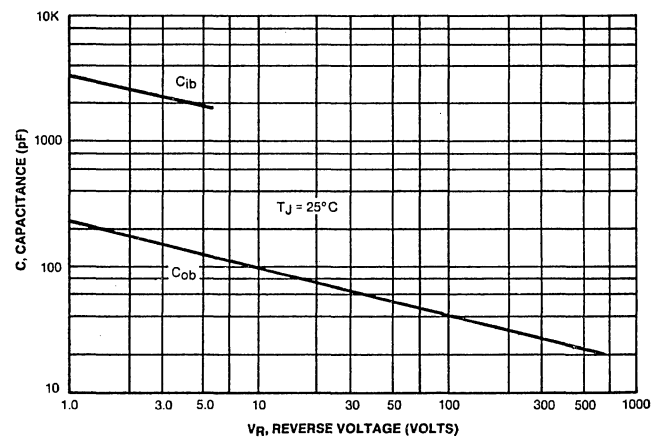


FIGURE 6 — CAPACITANCE

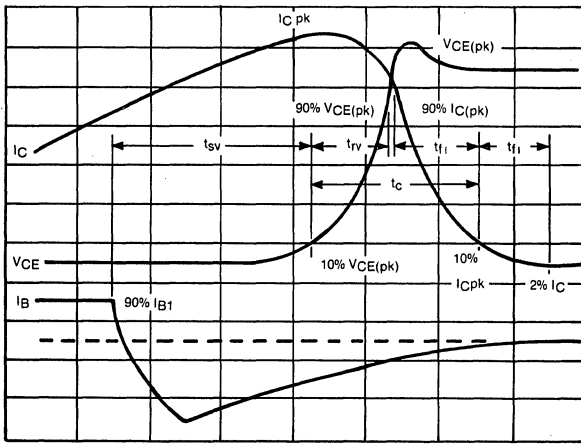


FIGURE 7 — INDUCTIVE SWITCHING MEASUREMENTS

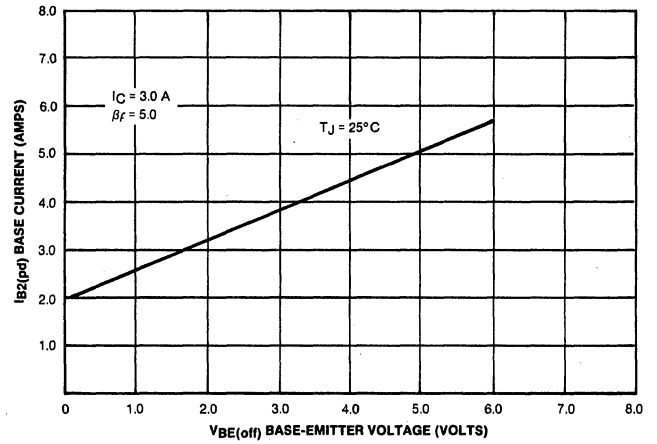


FIGURE 8 — PEAK REVERSE CURRENT

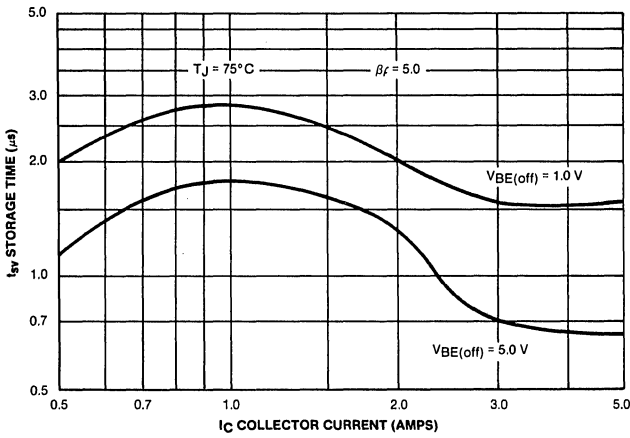


FIGURE 9 — STORAGE TIME

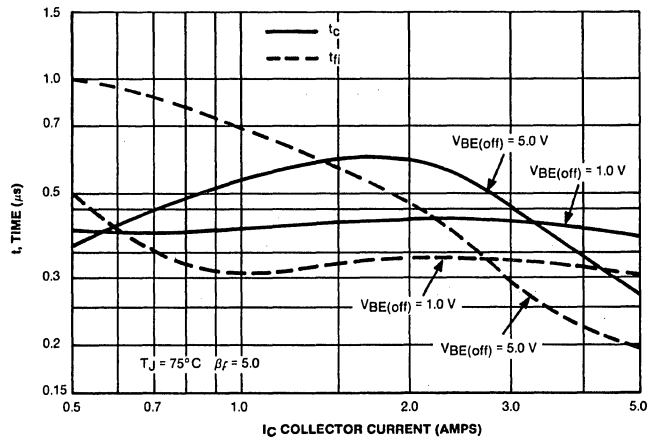


FIGURE 10 — CROSSOVER AND FALL TIMES

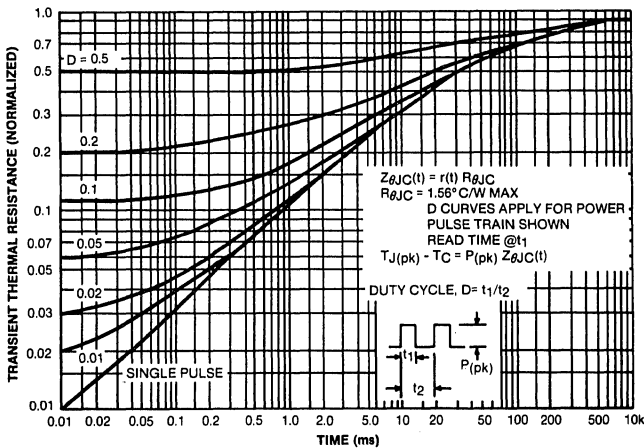


FIGURE 11 TYPICAL THERMAL RESPONSE [(Z_{θJC}(t))]

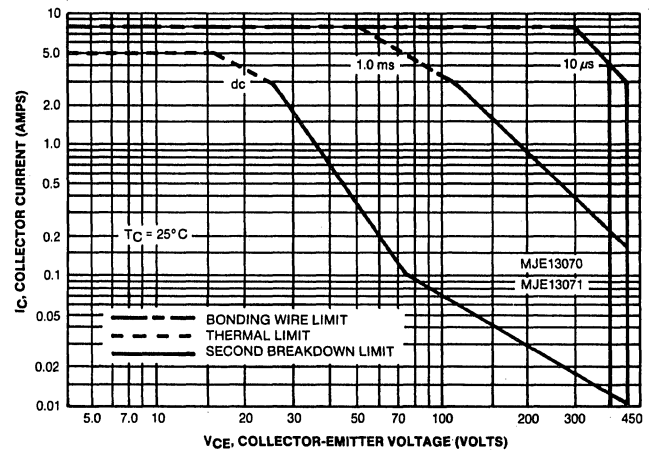


FIGURE 12 MAXIMUM FORWARD BIAS SAFE OPERATING AREA

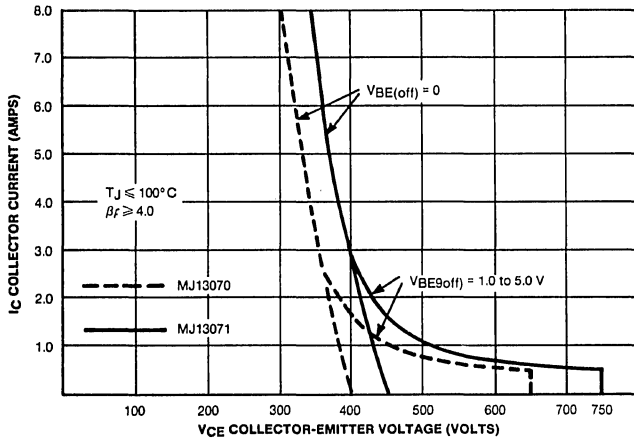


FIGURE 13 — MAXIMUM RATED REVERSE BIAS SAFE OPERATING AREA

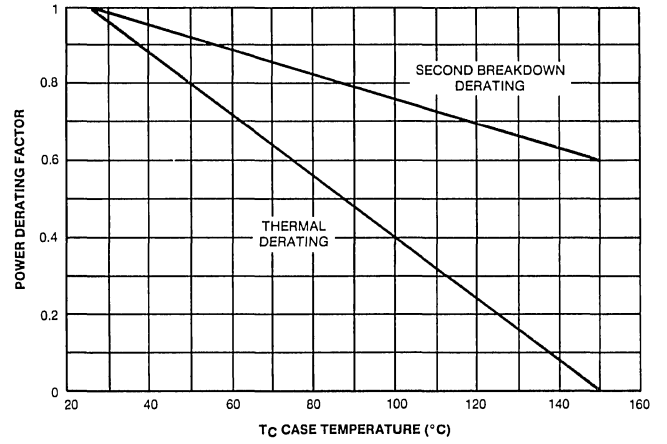


FIGURE 14 — POWER DERATING